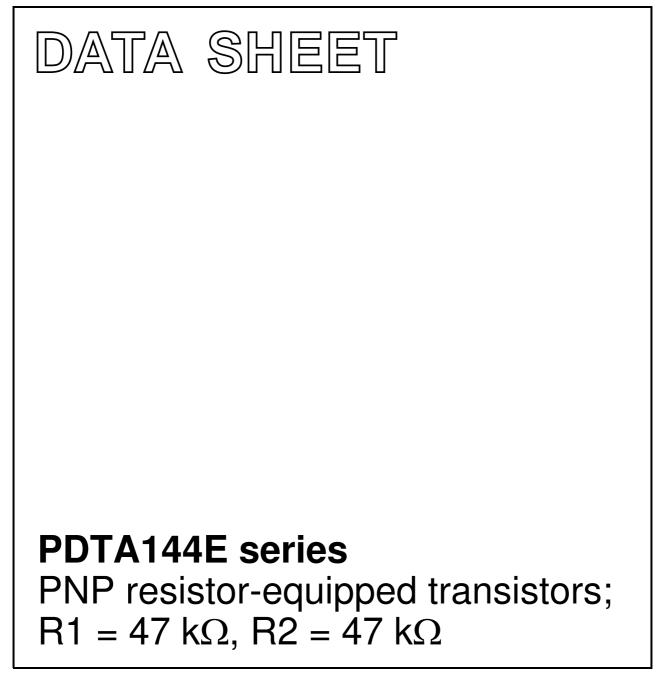
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2003 Apr 10 2004 Aug 05



## **PDTA144E series**

### FEATURES

- · Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

#### **APPLICATIONS**

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

**PRODUCT OVERVIEW** 

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	-	-50	V
lo	output current (DC)	-	-100	mA
R1	bias resistor	47	-	kΩ
R2	bias resistor	47	-	kΩ

### DESCRIPTION

PNP resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

	PACKAGE				
	PHILIPS	EIAJ	MARKING CODE	NPN COMPLEMENT	
PDTA144EE	SOT416	SC-75	07	PDTC144EE	
PDTA144EEF	SOT490	SC-89	07	PDTC144EEF	
PDTA144EK	SOT346	SC-59	07	PDTC144EK	
PDTA144EM	SOT883	SC-101	DR	PDTC144EM	
PDTA144ES	SOT54 (TO-92)	SC-43	TA144E	PDTC144ES	
PDTA144ET	SOT23	_	*07 <sup>(1)</sup>	PDTC144ET	
PDTA144EU	SOT323	SC-70	*07 <sup>(1)</sup>	PDTC144EU	

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.
  - \* = W: Made in China.

## PDTA144E series

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING		
ITPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PIN	DESCRIPTION		
PDTA144ES		1 2 3	base collector emitter		
PDTA144EE PDTA144EEF PDTA144EK PDTA144ET PDTA144EU	$\begin{array}{c} \hline 3 \\ \hline 1 \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline \end{array} \\ \hline \\ R2 \\ \hline \\ MDB271 \\ \hline \end{array} \\ \hline \end{array} \\ MDB271 \\ \hline \end{array}$	1 2 3	base emitter collector		
PDTA144EM	$2 \boxed{1} \\ 3 \\ Bottom view \\ MDB267 \\ 3 \\ MDD267 \\ 3 \\ MDC67 \\$	1 2 3	base emitter collector		

## PDTA144E series

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	-10	V
VI	input voltage				
	positive		—	+10	V
	negative		—	-40	V
lo	output current (DC)		-	-100	mA
I <sub>CM</sub>	peak collector current		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$			
	SOT54	note 1	—	500	mW
	SOT23	note 1	—	250	mW
	SOT346	note 1	—	250	mW
	SOT323	note 1	—	200	mW
	SOT416	note 1	—	150	mW
	SOT490	notes 1 and 2	_	250	mW
	SOT883	notes 2 and 3	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

#### Notes

- 1. Refer to standard mounting conditions.
- 2. Reflow soldering is the only recommended soldering method.
- 3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

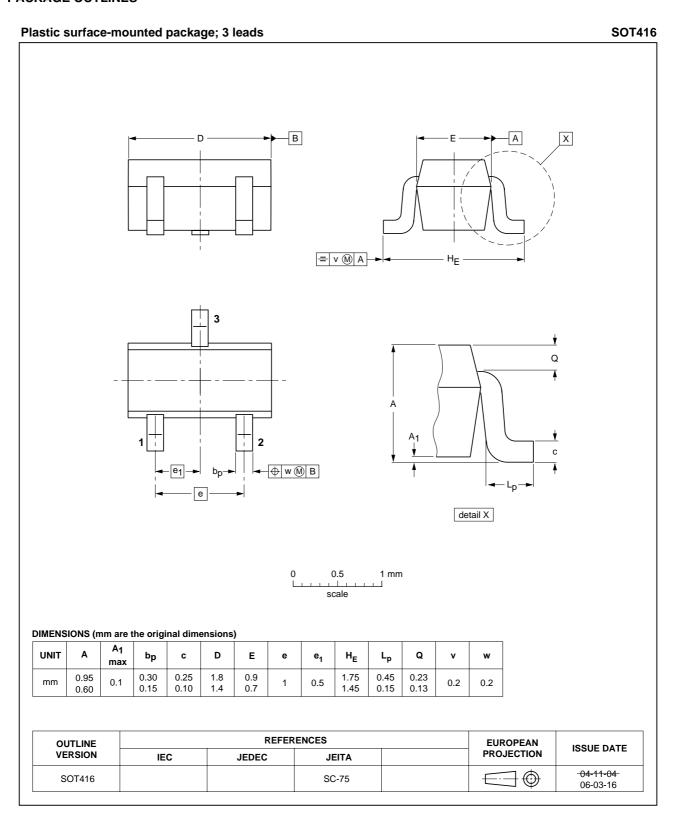
## PDTA144E series

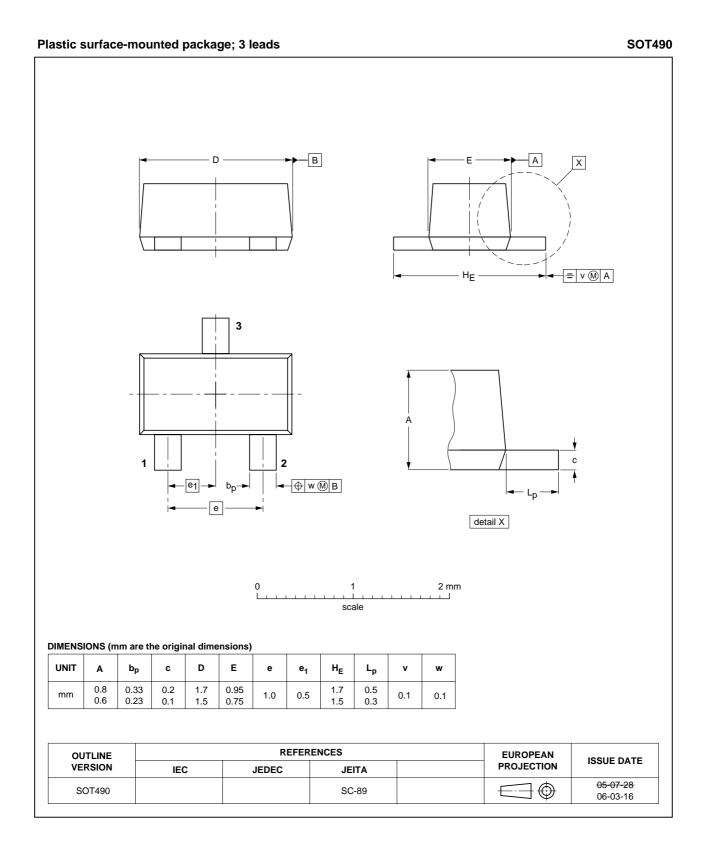
### CHARACTERISTICS

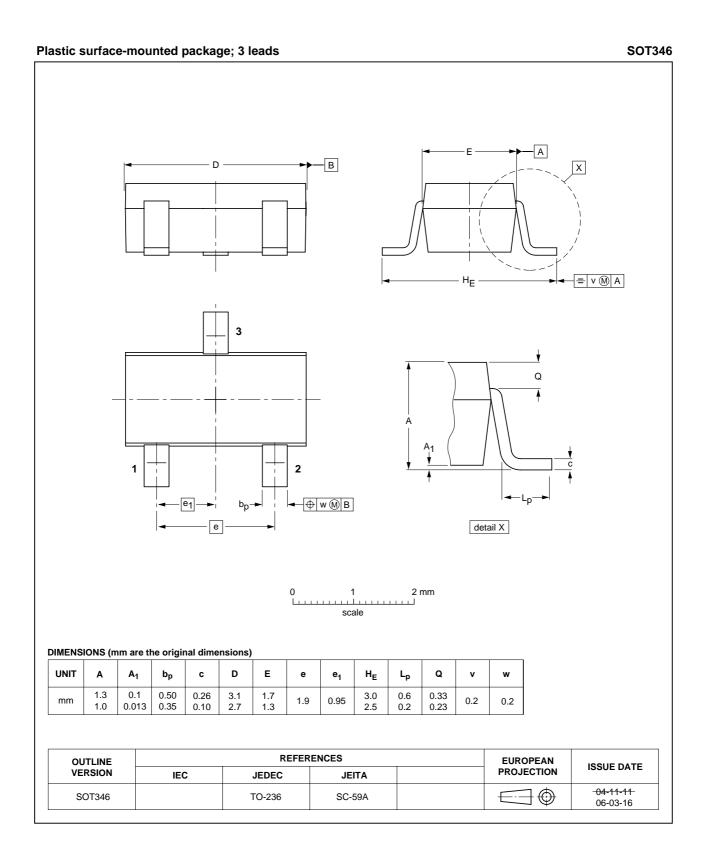
 $T_{amb}$  = 25 °C unless otherwise specified.

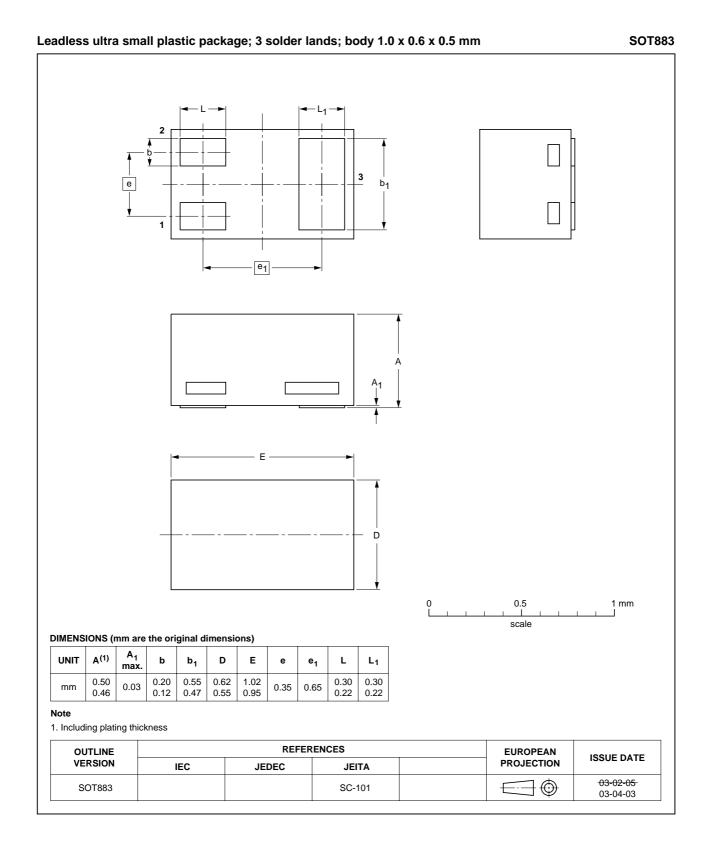
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0$	-	-	-100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	-	_	-1	μA
		$V_{CE} = -30 \text{ V}; I_B = 0; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0$	-	_	-90	μA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -5 \text{ mA}$	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA}; I_{B} = -0.5 \text{ mA}$	-	_	-150	mV
V <sub>i(off)</sub>	input-off voltage	$I_C = -100 \ \mu\text{A}; \ V_{CE} = -5 \ V$	_	-1.2	-0.8	V
V <sub>i(on)</sub>	input-on voltage	$I_{C} = -2 \text{ mA}; V_{CE} = -0.3 \text{ V}$	-3	-1.6	-	V
R1	input resistor		33	47	61	kΩ
<u>R2</u> R1	resistor ratio		0.8	1	1.2	
C <sub>c</sub>	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 V; f = 1 MHz$	_	-	3	pF

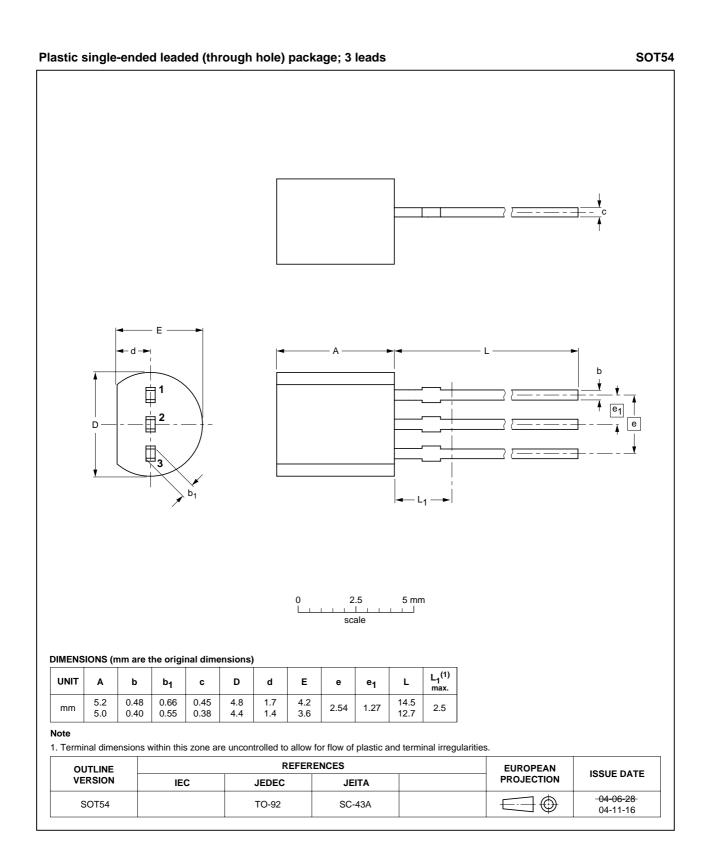
### PACKAGE OUTLINES

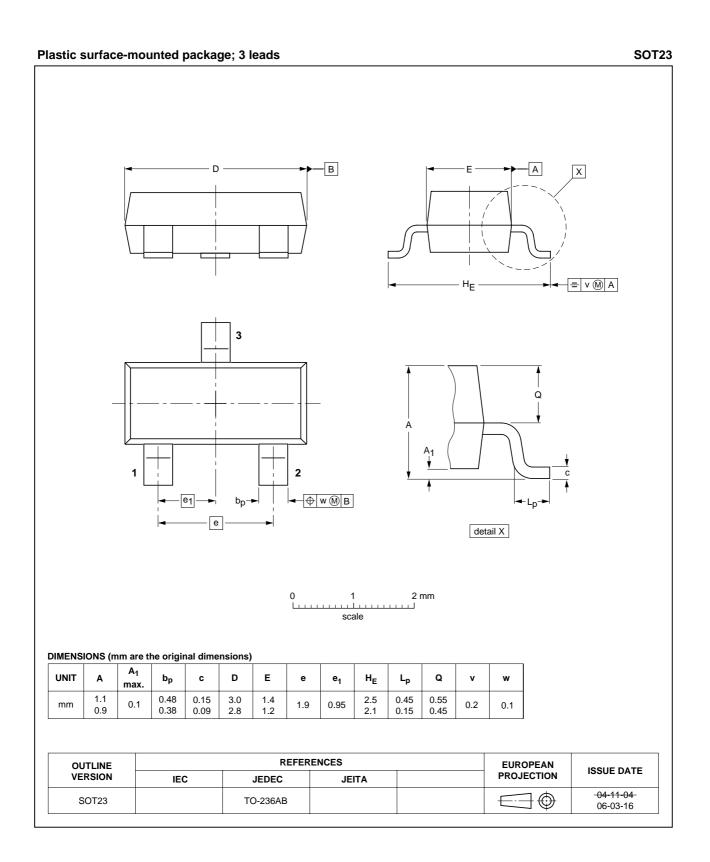


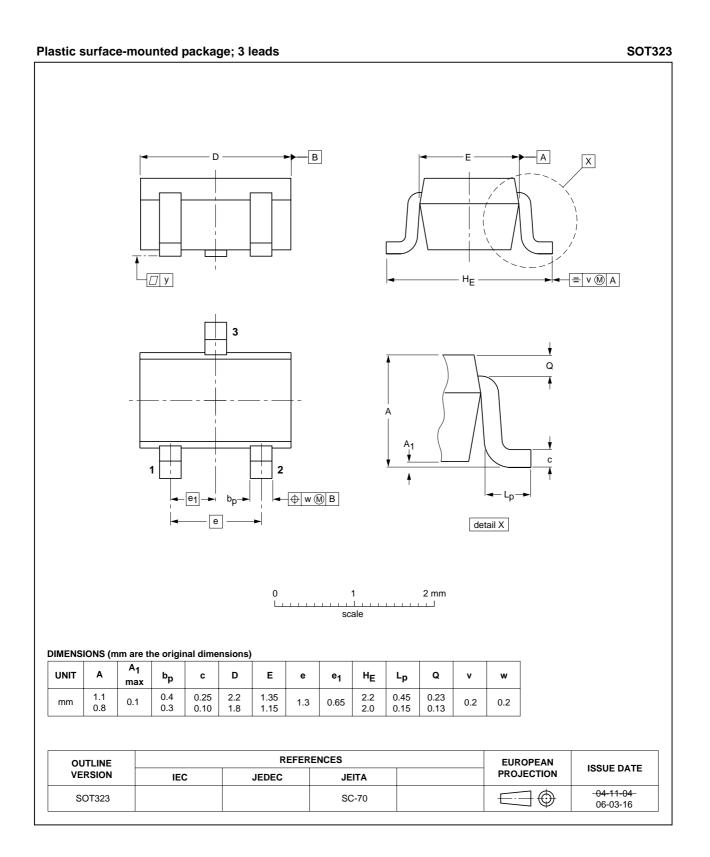












## PDTA144E series

#### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### DISCLAIMERS

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Terms and conditions of sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

## NXP Semiconductors

#### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

R75/07/pp14

Date of release: 2004 Aug 05

Document order number: 9397 750 13659

